# MSKSEMI 美森科













**ESD** 

TSS

MOV

**GDT** 

PLED

# **SP3010-04UTG-MS**

Product specification





#### **Features**

- 60Watts peak pulse power (tp = 8/20µs)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.2pF typ. I/O to I/O)
- IEC 61000-4-2 ±20kV contact ±25kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20μs)

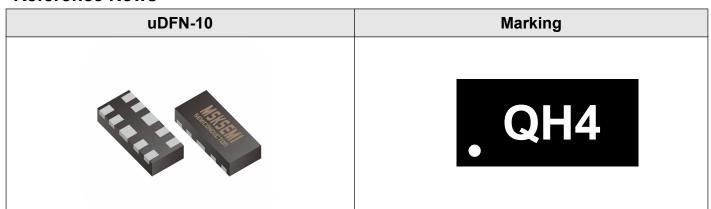
#### **Mechanical Data**

- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

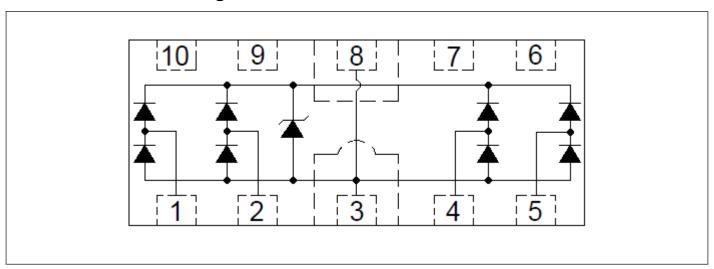
#### **Applications**

- USB3.0, USB2.0, Ethernet
- HDMI 2.0, Displayport 1.3,eSATA
- Unified Display interface
- Digital Visual Interface
- High speed serial interface

#### **Reference News**



#### **Schematic & PIN Configuration**



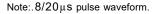


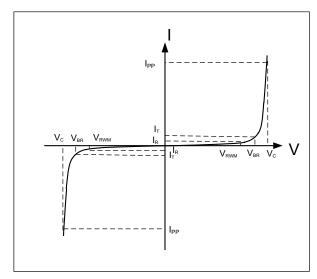
#### **Electrical Characteristics**

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	l <sub>T</sub> =1mA	6.0			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =5V,T=25℃			1	μА
Peak Pulse Current	I <sub>PP</sub>	tp =8/20μs			4	А
Clamping Voltage	Vc	I <sub>PP</sub> =4A,t <sub>p</sub> =8/20μs			15	V
Junction Capacitance	Cj	V <sub>R</sub> = 0V, f = 1MHz I/O to I/O		0.2	0.3	pF
		V <sub>R</sub> = 0V, f = 1MHz I/O to GND		0.4	0.55	

## Electrical Parameters (TA = 25°C unless otherwise noted)

	Parameter		
<b>I</b> PP	MaximumReversePeak Pulse Current		
Vc	Clamping Voltage @ IPP		
VRWM	WorkingPeak Reverse Voltage		
<b>I</b> R	Maximum Reverse Leakage Current @ VRWM		
VBR	Breakdown Voltage @ Ιτ		
lτ	Test Current		







## **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

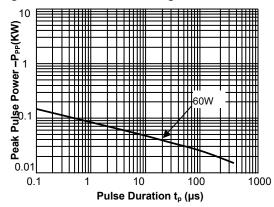


Fig.2 Pulse Derating Curve

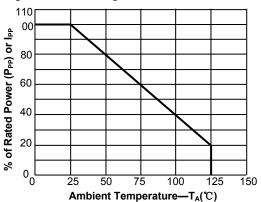


Fig.3 Pulse Waveform-8/20µs

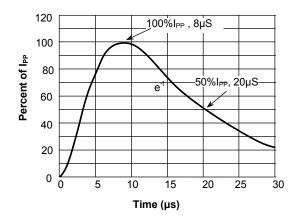
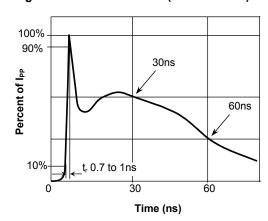


Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





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